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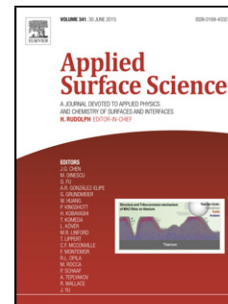

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ACCEPTED MANUSCRIPT

Analysis of arrayed nanocapacitor formed on nanorods by flow-rate interruption atomic layer deposition

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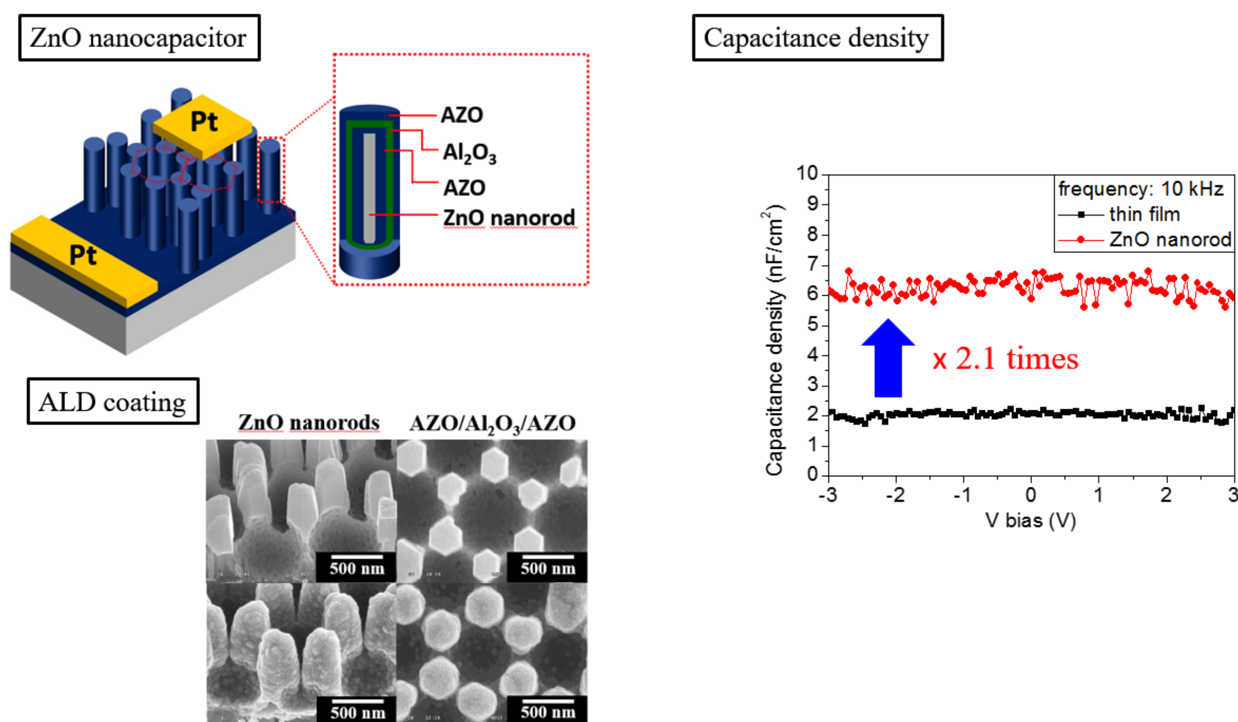
Graphical abstract



Highlights

- High quality Al_2O_3 was deposited by flow-rate interruption atomic layer deposition.
- Nanocapacitor was fabricated on vertical and well-aligned ZnO arrays.
- *ZnO array enhance energy storage capability by providing significant surface area.*
- Nanocapacitor shows 100 % increased capacitance density than thin film structure.

Abstract

Flow-rate interruption (FRI) atomic layer deposition (ALD) technique was adopted to

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